

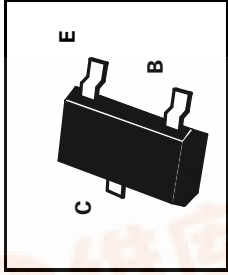
# SOT23 NPN SILICON PLANAR HIGH VOLTAGE TRANSISTORS

**FM5550**  
**FM5551**

ISSUE 4 - NOVEMBER 1996

PARTMARKING DETAILS - FM5550 - 1FZ  
FM5551 - ZG1

COMPLEMENTARY TYPES - FM5550 - FM5550  
FM5551 - FM5551



## ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	FM5550	FM5551	UNIT
Collector-Base Voltage	$V_{CB0}$	160	180	V
Collector-Emitter Voltage	$V_{CE0}$	140	160	V
Emitter-Base Voltage	$V_{EB0}$	6	6	V
Continuous Collector Current	$I_C$	600	600	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	$P_{Tot}$	330	330	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150		$^{\circ}C$

## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ ).

PARAMETER	SYMBOL	FM5550		FM5551		CONDITIONS.
		MIN.	MAX.	MIN.	MAX.	
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	160		180		$I_C=100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	140		160		$I_C=1mA$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6		6		$I_E=10\mu A^*$
Collector Cut-Off Current	$I_{CBO}$		100 100			$V_{CB}=100V$ $V_{CB}=100V, T_A=100^{\circ}C$ $V_{CB}=120V$ $V_{CB}=120V, T_A=100^{\circ}C$
Static Forward Current Transfer Ratio	$h_{FE}$	60 60 20	250	80 80 30	250	$I_C=1mA, V_{CE}=5V$ $I_C=10mA, V_{CE}=5V$ $I_C=50mA, V_{CE}=5V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.15 0.25		0.15 0.20	$I_C=10mA, I_B=1mA$ $I_C=50mA, I_B=5mA$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		1.0 1.2		1.0 1.2	$I_C=10mA, I_B=1mA$ $I_C=50mA, I_B=5mA$
Transition Frequency	$f_T$	100	300	100	300	$I_C=10mA, V_{CE}=10V$ $f=100MHz$
Output Capacitance	$C_{ob0}$		6.0		6.0	$V_{CB}=10V, f=1MHz$
Small Signal	$h_{fe}$	50	200	50	260	$I_C=1mA, V_{CE}=10V$ $f=1KHz$
Noise Figure	NF		10		8	$I_C=250\mu A, V_{CE}=5V,$ $R_S=1K\Omega$ $f=10Hz$ to $15.7KHz$

\* Periodic Sample Test Only

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